

SAMYANG ELECTRONICS MBRF1535CT --- MBRF15200CT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- $\diamondsuit\mbox{Low}$ forward voltage drop,low switching losses
- \diamondsuit High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- \bigcirc The plastic material carries U/L $\,$ recognition 94V-0 $\,$

MECHANICAL DATA

- - MIL-STD-750,Method 2026
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

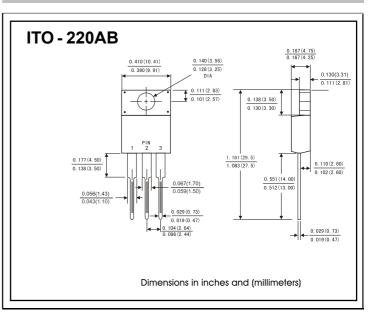
		Symbols	MBRF 1535CT	MBRF 1545CT	MBRF 1550CT	MBRF 1560CT	MBRF 15100CT	MBRF 15150CT	MBRF 15200CT	Units
Maximum repetitive peak reverse voltage		Vrrm	35	45	50	60	100	150	200	Volts
Maximum RMS voltage		Vrms	25	32	35	42	70	105	140	Volts
Maximum DC blocking voltage		Vdc	35	45	50	60	100	150	200	Volts
Maximum average forward rectified current(see Fig.1)	Per leg Total device	I(AV)	7.5 15.0						Amps	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		FSM	150.0							Amps
Maximum instantaneous forward voltage at 15 A		VF	0.60		().75	0.85	0. 90	0. 95	Volts
Maximum instantaneous reverse	T _c =25°C	I	0.2							
current at rated DC blocking voltage(Note 1)	$T_c = 125^{\circ}C$	R	30			50				mA
Typical thermal resistance (Note 2)		R _θ JC	3.0							°C/W
Operating junction temperature range		TJ	-65 to+150							°C
Storage temperature range		Tsig	-65 to+150							°C

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

VOLTAGE RANGE: 35 --- 200 V CURRENT:15.0A



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